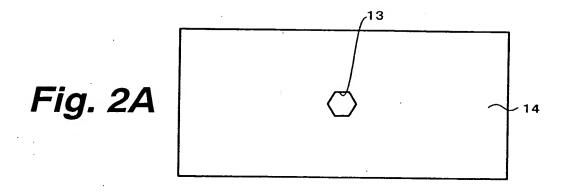
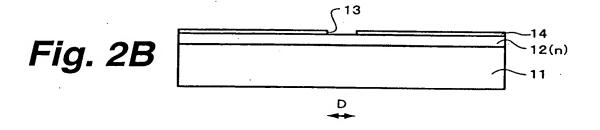
Fig. 1A

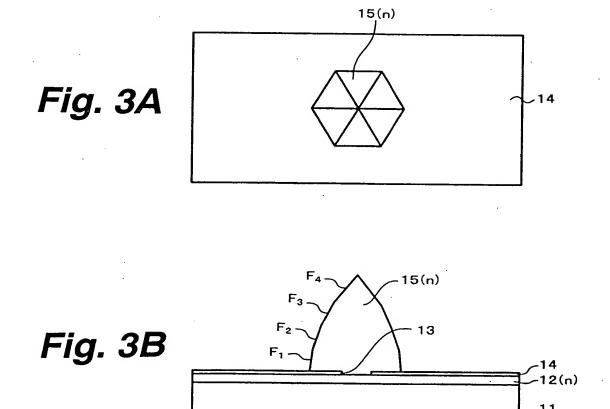
107(p)
104

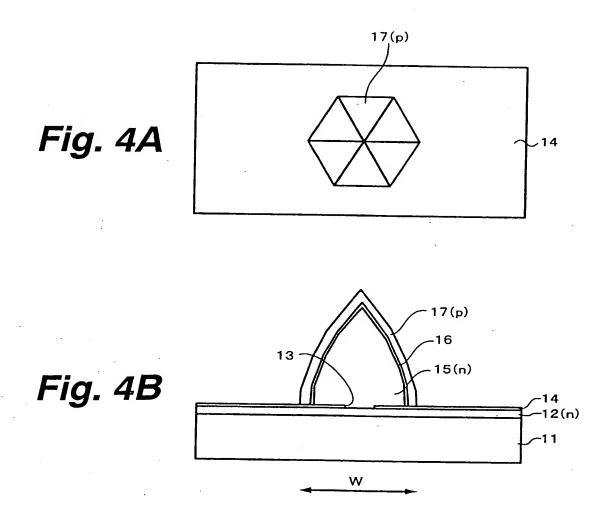
Fig. 1B

107(p)
106
106
109
101
101









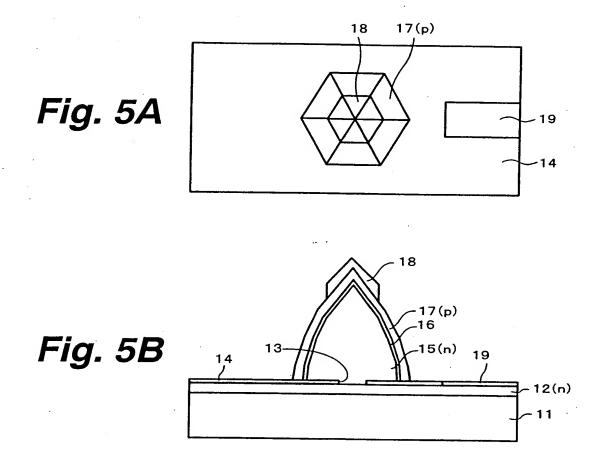
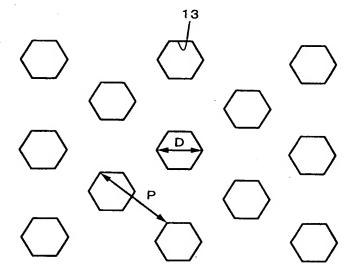
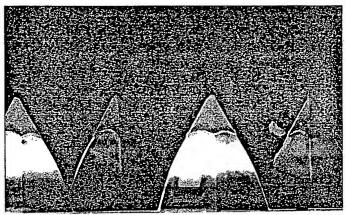


Fig. 6



## Fig. 7



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Fig. 8

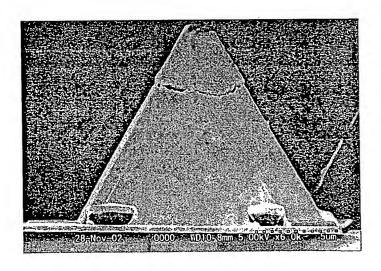


Fig. 9

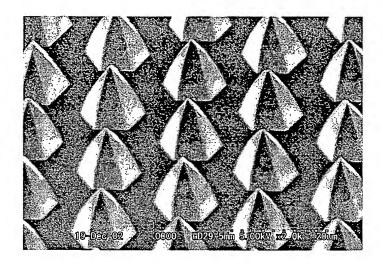


Fig. 10

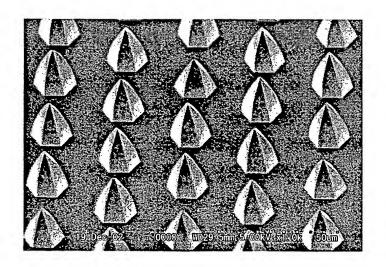


Fig. 11

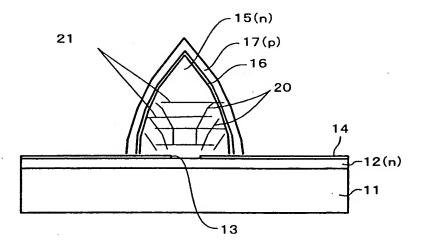


Fig. 12

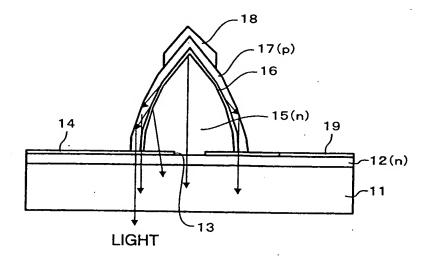


Fig. 13

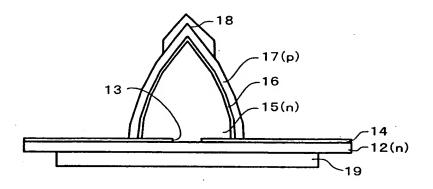


Fig. 14

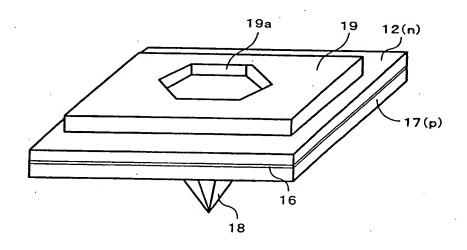
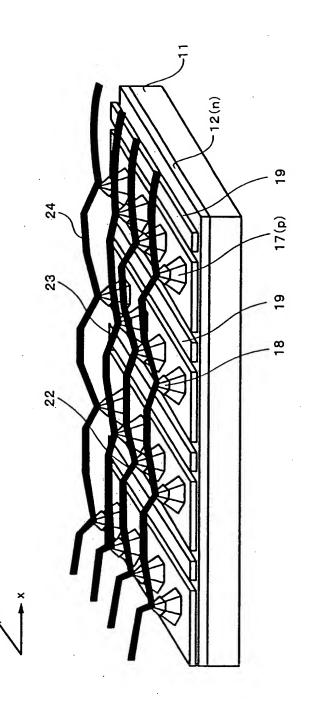
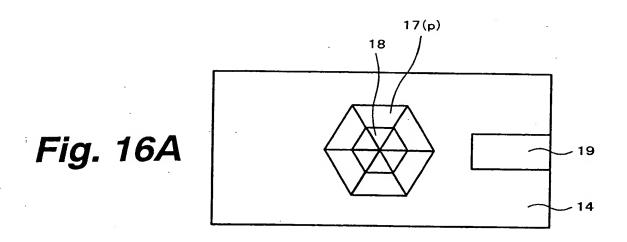
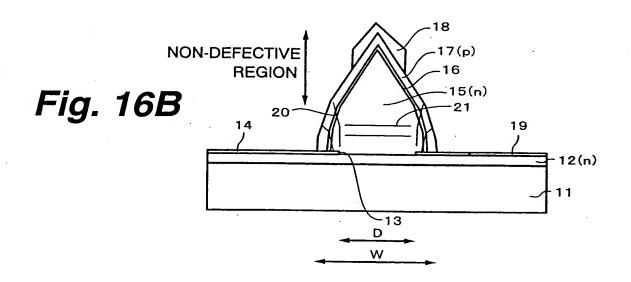
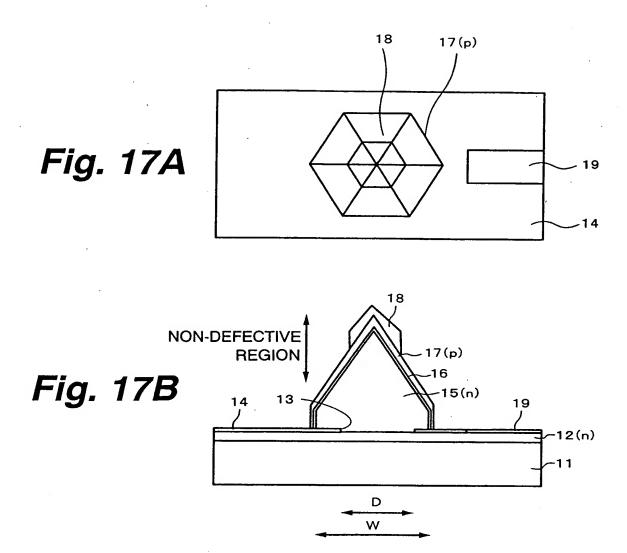


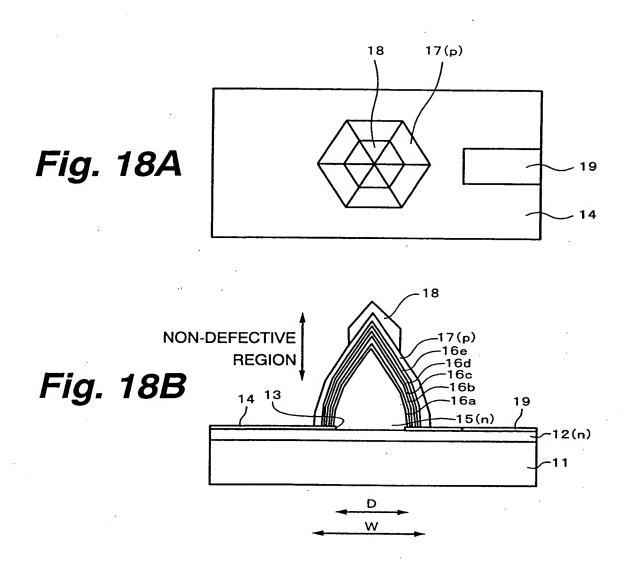
Fig. 15

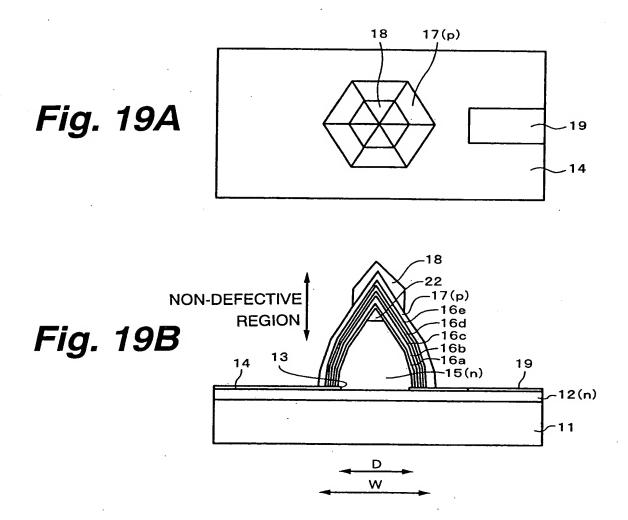


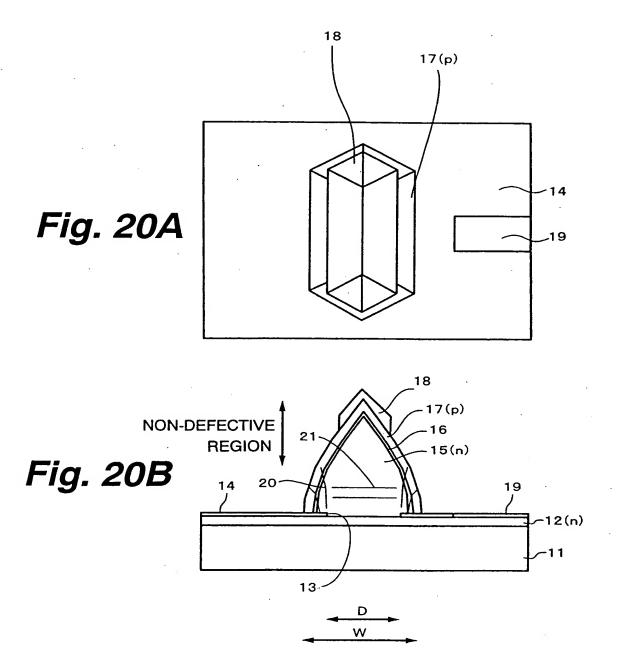


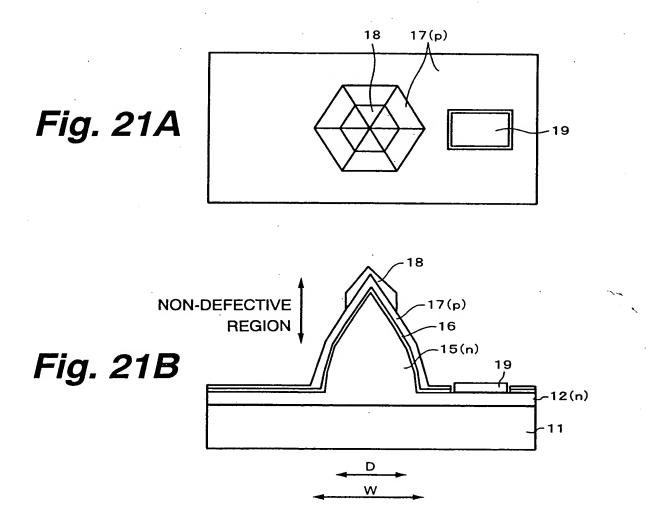












## DESCRIPTION OF REFERENCE NUMERALS

11	SAPPHIRE SUBSTRATE
12	n-TYPE GaN LAYER
13	OPENING
14	GROWTH MASK
15	n-TYPE GaN LAYER
16	ACTIVE LAYER
17	p-TYPE GaN LAYER
18	p-SIDE ELECTRODE
19	n-SIDE ELECTRODE